SILICON NPN TRANSISTORS

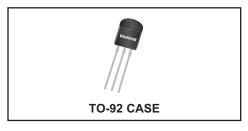


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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N4400 and 2N4401 are silicon NPN transistors designed for general purpose amplifier and switching applications. PNP complementary types are 2N4402 and 2N4403.





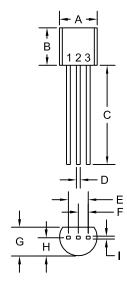
MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Continuous Collector Current	l _C	600	mA
Power Dissipation	P_{D}	625	mW
Operating and Storage Junction Temperature	T _J , T _{sta}	-65 to +150	°C

ELECTRICAL	CHARACTERISTICS: (T _A =25°C)	2N4	<u> 1400</u>	2N4	<u>401</u>	
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNITS
ICEV	V_{CE} =35V, V_{EB} =0.4V	-	100	-	100	nA
BV _{CBO}	I _C =0.1mA	60	-	60	-	V
BV _{CEO}	I _C =1.0mA	40	-	40	-	V
BVEBO	I _E =0.1mA	6.0	-	6.0	-	V
V _{CE} (SAT)	I _C =150mA, I _B =15mA	-	0.40	-	0.40	V
VCE(SAT)	I _C =500mA, I _B =50mA	-	0.75	-	0.75	V
V _{BE} (SAT)	I _C =150mA, I _B =15mA	0.75	0.95	0.75	0.95	V
V _{BE} (SAT)	I _C =500mA, I _B =50mA	-	1.2	-	1.2	V
h _{FE}	V _{CE} =1.0V, I _C =0.1mA	-	-	20	-	
hFE	V _{CE} =1.0V, I _C =1.0mA	20	-	40	-	
hFE	V _{CE} =1.0V, I _C =10mA	40	-	80	-	
hFE	V _{CE} =1.0V, I _C =150mA	50	150	100	300	
hFE	V _{CE} =2.0V, I _C =500mA	20	-	40	-	
h _{fe}	V _{CE} =10V, I _C =1.0mA, f=1.0kHz	20	250	40	500	
f_T	V _{CE} =10V, I _C =20mA, f=100MHz	200	-	250	-	MHz
C _{ob}	V _{CB} =5.0V, I _E =0, f=100kHz	-	6.5	-	6.5	pF
C _{ib}	V _{BE} =0.5V, I _C =0, f=100kHz	-	30	-	30	pF
ton	V _{CC} =30V, V _{EB(OFF)} =2.0V, I _C =150mA,					
	I _{B1} =15mA	-	35	-	35	ns
t _{off}	V_{CC} =30V, I_{C} =150mA, I_{B1} = I_{B2} =15mA	-	255	-	255	ns

SILICON **NPN TRANSISTORS**



TO-92 CASE - MECHANICAL OUTLINE



DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
A (DIA)	0.175	0.205	4.45	5.21		
В	0.170	0.210	4.32	5.33		
С	0.500	-	12.70	-		
D	0.016	0.022	0.41	0.56		
E	0.100		2.54			
F	0.050		1.27			
G	0.125	0.165	3.18	4.19		
Н	0.080	0.105	2.03	2.67		
l	0.015		0.38			

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter 2) Base
- 3) Collector

MARKING:

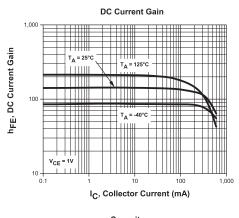
R1

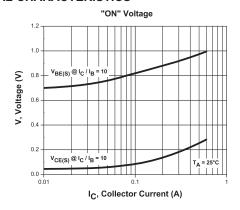
FULL PART NUMBER

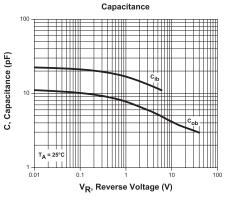
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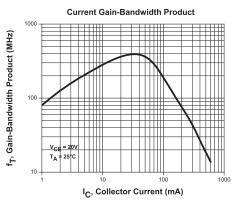


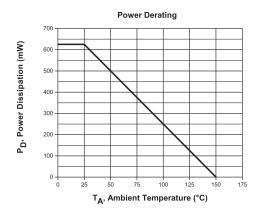
TYPICAL ELECTRICAL CHARACTERISTICS











R2 (2-December 2014)

SILICON NPN TRANSISTORS



SERVICES

- · Bonded Inventory
- · Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/Multi Discrete Modules (MDM™)
- · Bare Die Available for Hybrid Applications

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R2 (2-December 2014)